

PXD6 Technology status

22.9.2009

● Relevant process sequence



ALIN - Alignment marks

POXP - backside boron implant

Wafer bonding

Thermal Oxidation

Front/backside alignment

Global HE implantation (unmasked)

done

Nitride deposition

done

Polysilicon deposition

done

introduction of a polysilicon option

LTO deposition

done

Polysilicon doping (outside implantation)

Polysilicon annealing

PO1N polysilicon photolithography and etching

wet etching

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plasma etch

● Yield problem I - Polysilicon roughness

Poly I + II edges and surfaces

